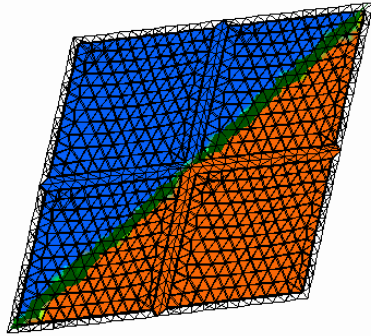

Micromagnetic Simulation of Domain Wall Pinning and Domain Wall Motion

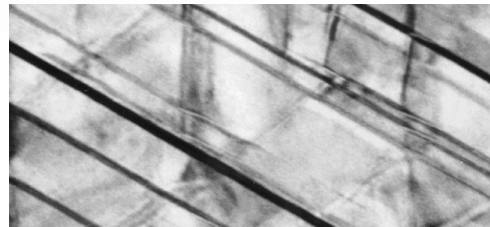
W Scholz, H Forster, J Fidler, T Schrefl
Vienna University of Technology

Outline



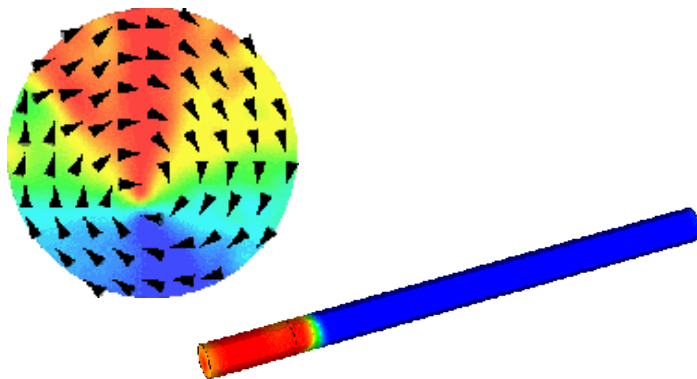
Introduction

Finite element method



Domain Wall Pinning

Pinning controlled SmCo magnets

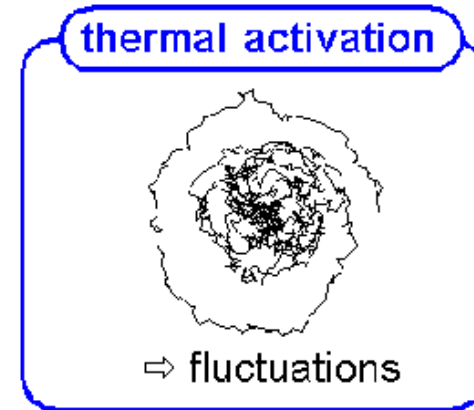
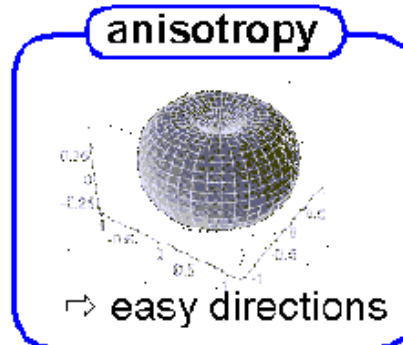
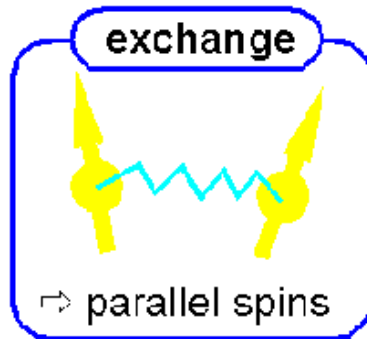


Nano-wires

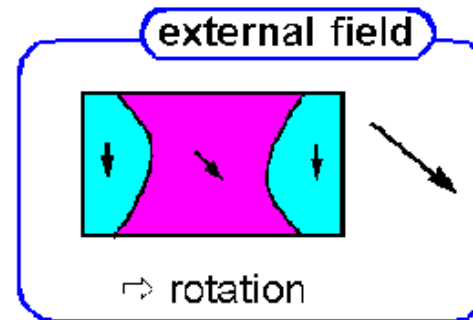
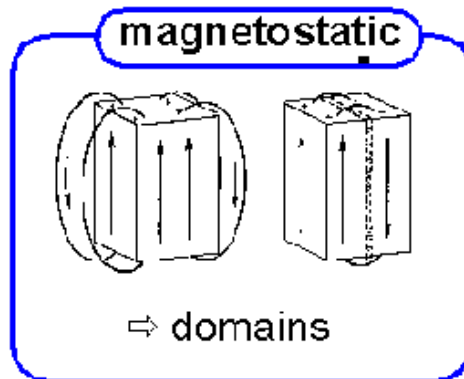
Domain wall velocities

Summary

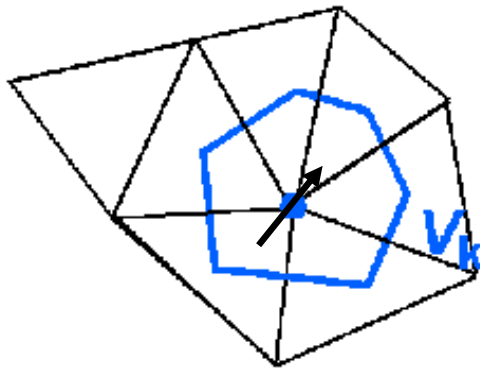
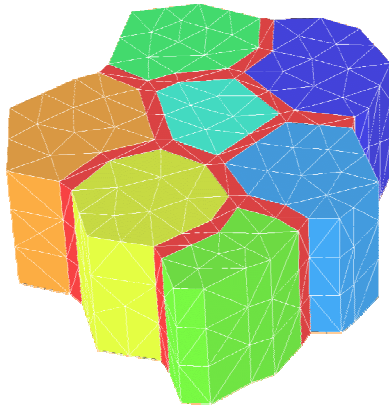
Micromagnetics



$$\frac{\partial \mathbf{J}}{\partial t} = -\gamma \mathbf{J} \times (\mathbf{H}_{\text{eff}} + \mathbf{H}_{\text{th}}) + \frac{\alpha}{J_s} \mathbf{J} \times \frac{\partial \mathbf{J}}{\partial t}$$



Finite Element Approach



- divide particles into finite elements
⇒ triangles, tetrahedrons
- expand \mathbf{J} with basis function φ

$$\vec{J}(\vec{x}) = \sum_{i=1}^{nodes} \vec{J}_i \varphi_i(\vec{x})$$

- energy as a function of $\mathbf{J}_1, \mathbf{J}_2 \dots \mathbf{J}_N$

$$E(\vec{J}_1, \vec{J}_2 \dots \vec{J}_N)$$

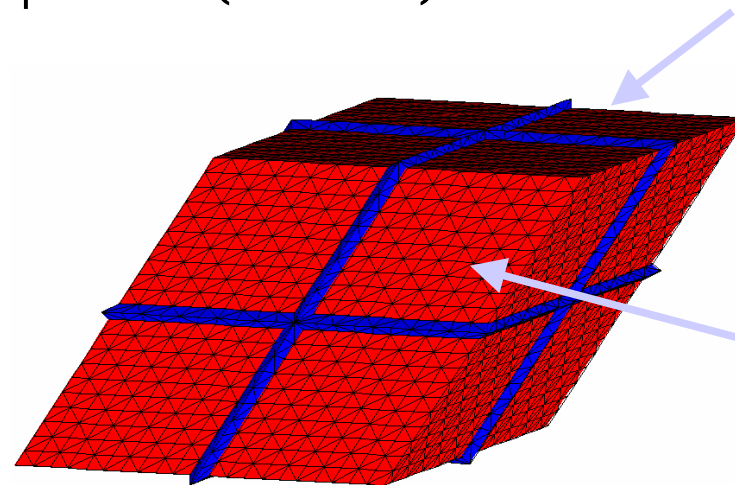
- effective field

$$\vec{H}_k = -\frac{1}{V_k} \frac{\partial E(\vec{J}_1, \vec{J}_2 \dots \vec{J}_N)}{\partial \vec{J}_k}$$

- ⇒ effective field on irregular grids
- ⇒ rigid magnetic moment
at the **nodes**

Magnetostatic Field Calculation

- ▶ magnetic scalar potential
 $\mathbf{H} = -\nabla U$
- ▶ solve Gilbert equation *simultaneously* with
 - ⇒ Poisson equation (inside)
 - ⇒ Laplace equation (outside)



**boundary element
method (BEM)**

**finite element
method (FEM)**

BEM leads to a fully populated $N \times N$ matrix

- ⇒ N ... number of nodes at the surface
- ⇒ matrix compression using wavelets

Pinning Controlled SmCo Magnets

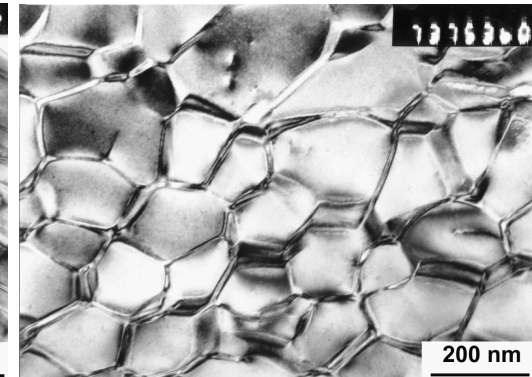
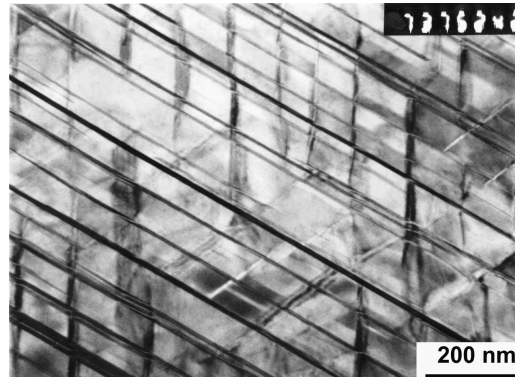
- Characterization of SmCo permanent magnets by transmission electron microscopy

Microstructure

- Composition
- Heat treatment
- Additives

influence

- Precipitation structure
- Lamella phase
- Cell size

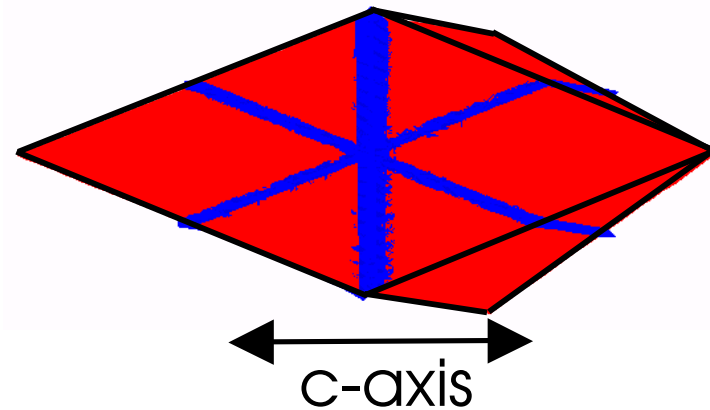
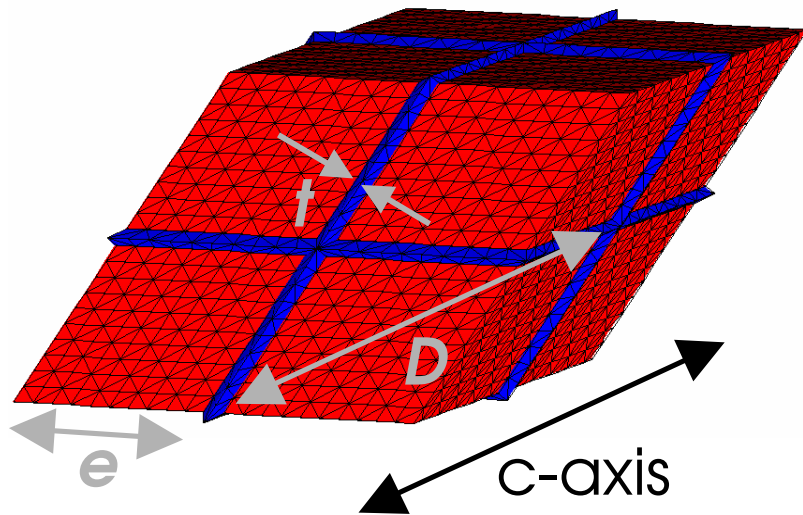


- Lorentz image of two magnetic domains

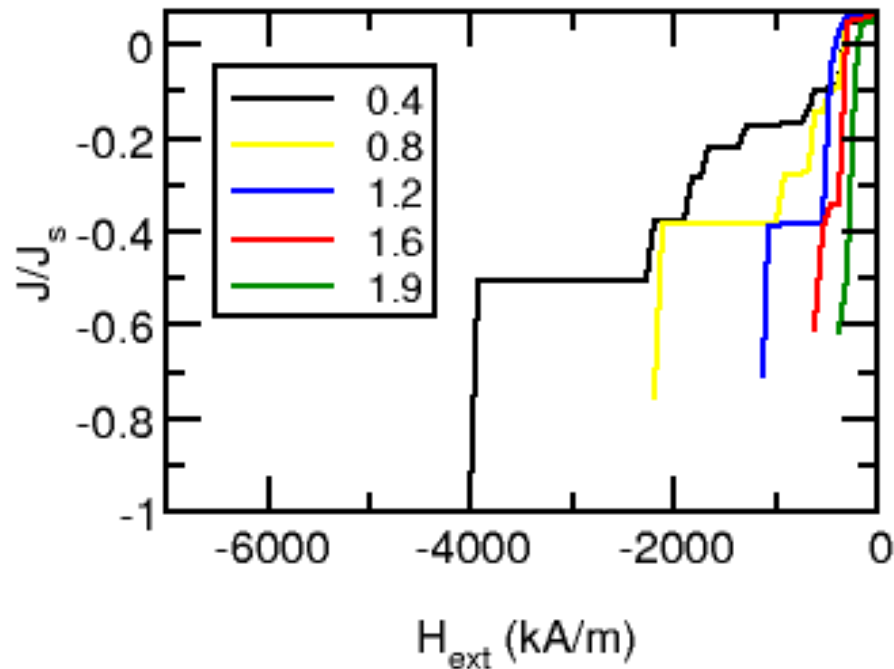


Micromagnetic Model

- Finite element mesh:
15833 nodes
84749 tetrahedral elements
7056 surface elements
- Resolution of the mesh:
 $e/10 = D/25$
for $D = 125 \text{ nm}$: 5 nm
 $\delta(\text{Sm}_2\text{Co}_{17}) = 5 \text{ nm}$

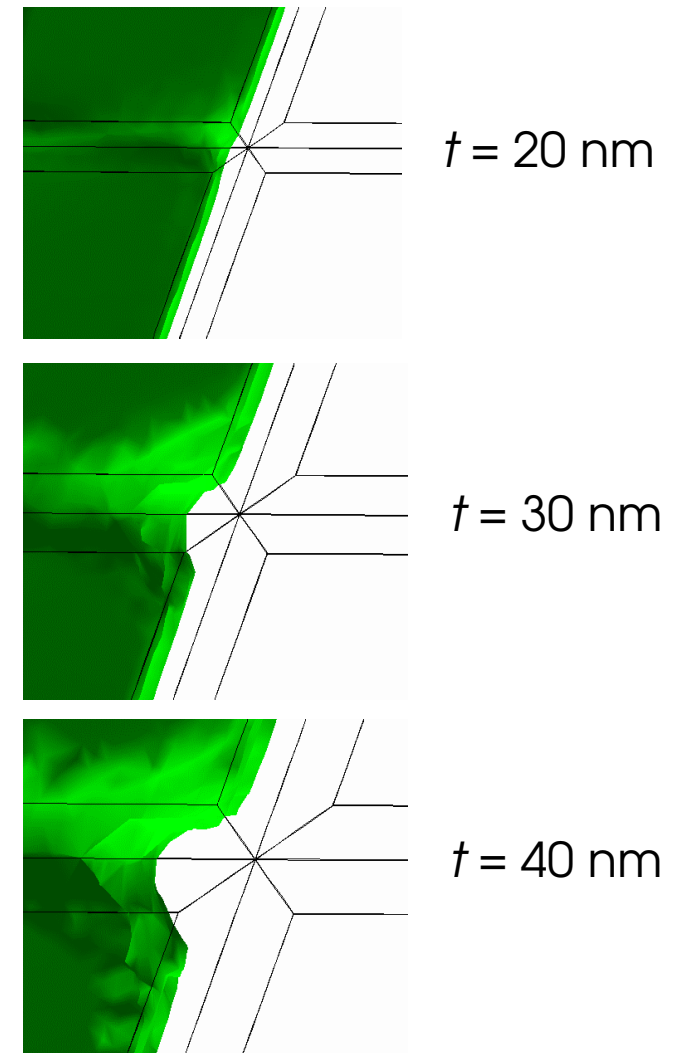


Attractive Pinning



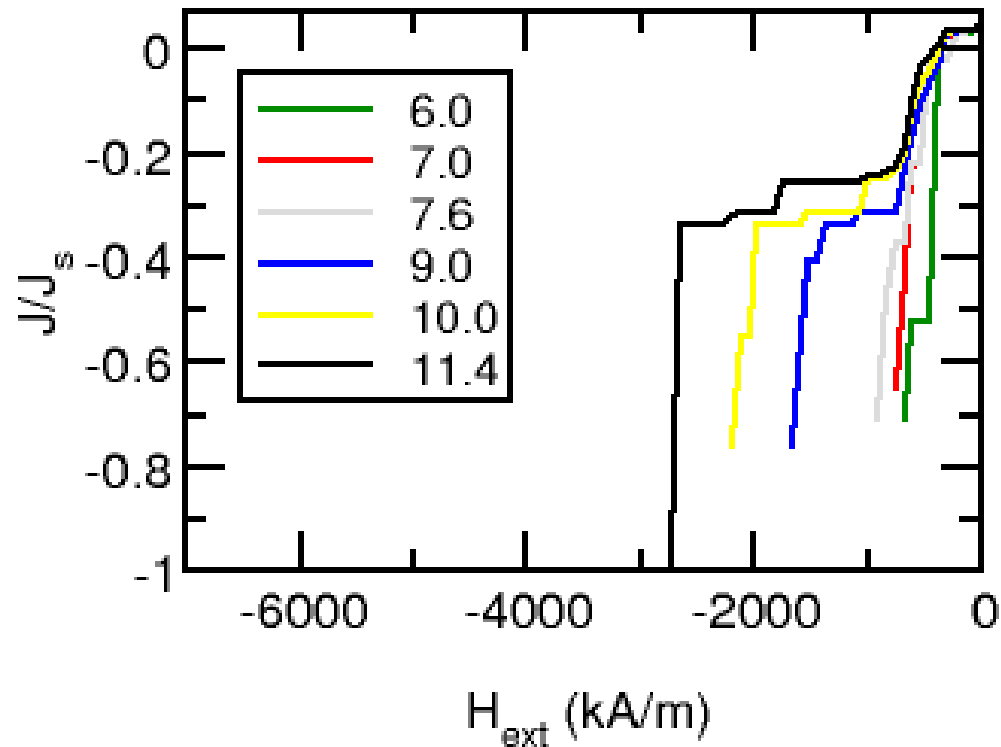
- Cells ($\text{Sm}_2\text{Co}_{17}$):
Polarization: $J_s = 1.32$ T
Anisotropy: $K_1 = 5$ MJ/m³
Exchange: $A = 14$ pJ/m
- Intercellular phase:
Polarization: $J_s = 0.8$ T
Anisotropy: $K_1 = 1.2$ MJ/m³
Exchange: $A = 14$ pJ/m

Domain wall bending

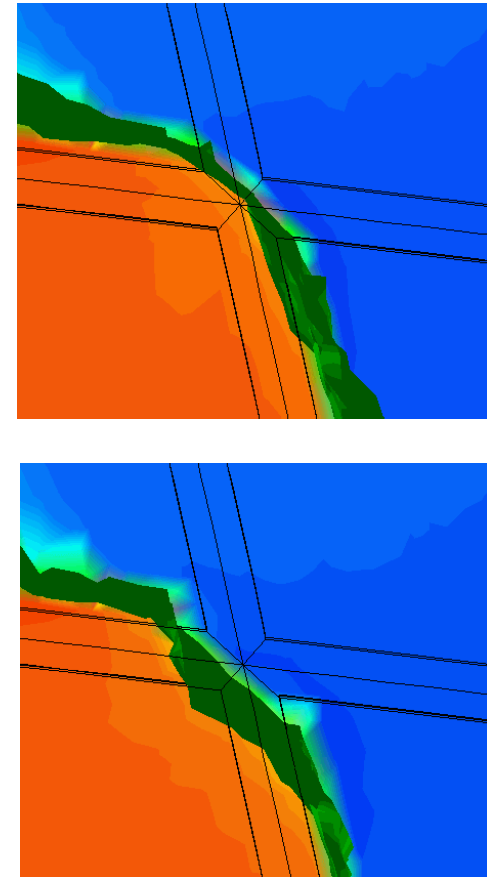


Repulsive Pinning

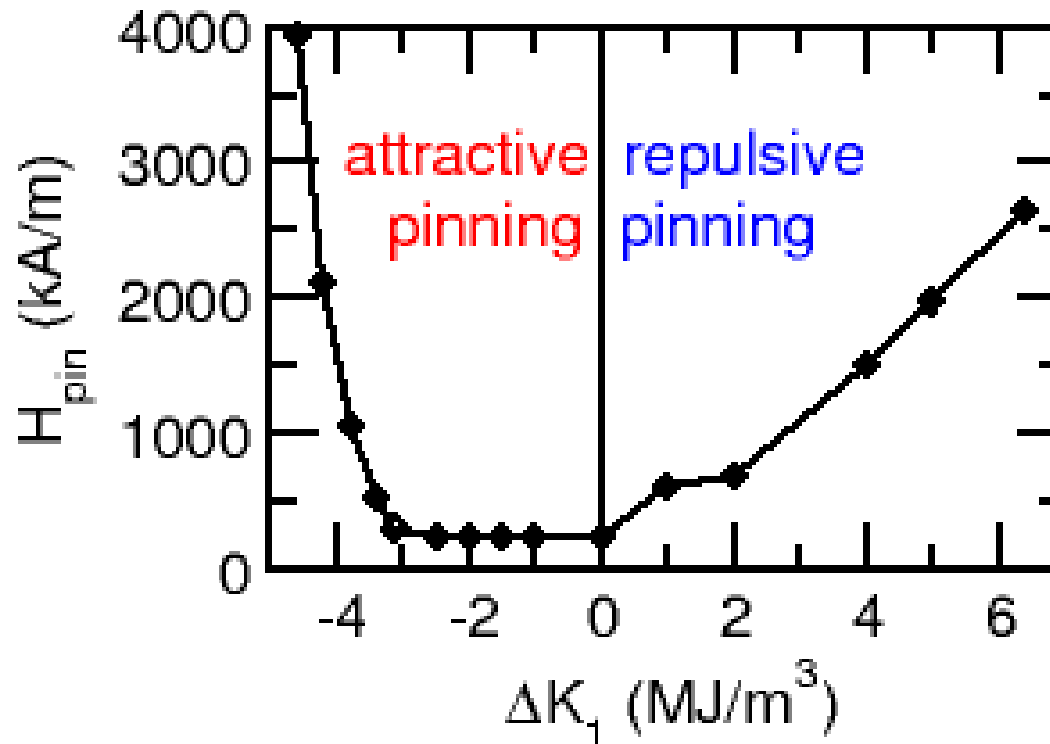
- Cells: $D = 125$ nm
- Intercellular phase:
Thickness: $t = 10$ nm
Anisotropy: $K_1 = 9$ MJ/m³



Domain wall depinning



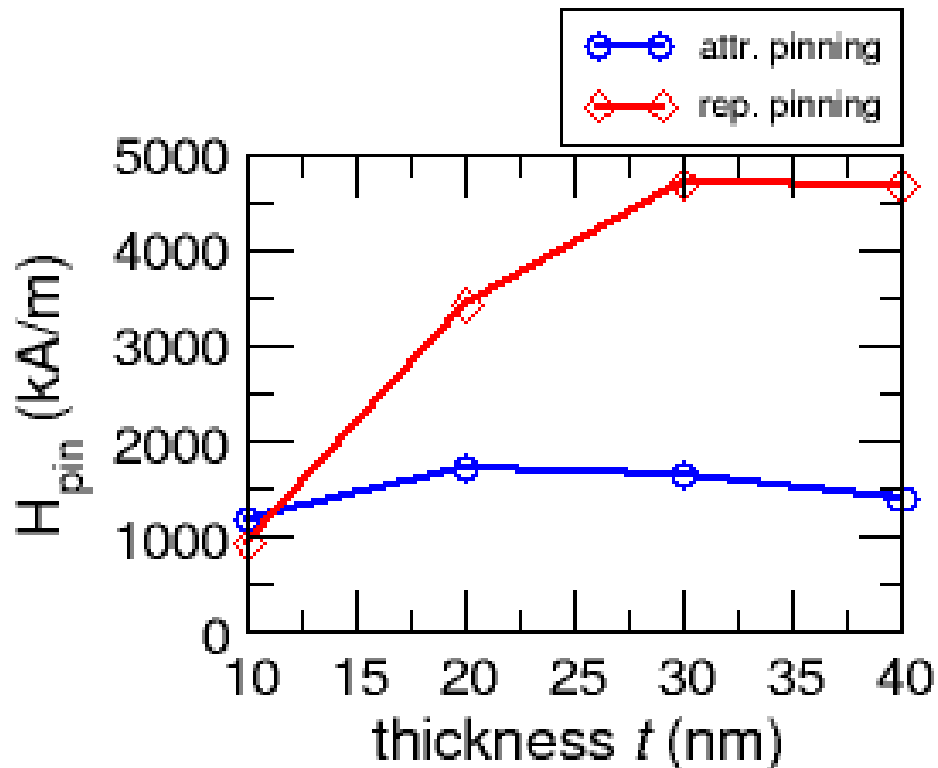
Pinning Fields



- Linear behaviour in the regime of repulsive pinning in agreement with a simple analytical 1D-model by Kronmüller (IEEE Trans. Magn. MAG-20 (1984) 1569):

$$H_c^{\max} = \alpha(K_1^{\text{phase}} - K_1^{\text{cells}}) / M_s^{\text{cells}}$$

Variation of the Phase Thickness



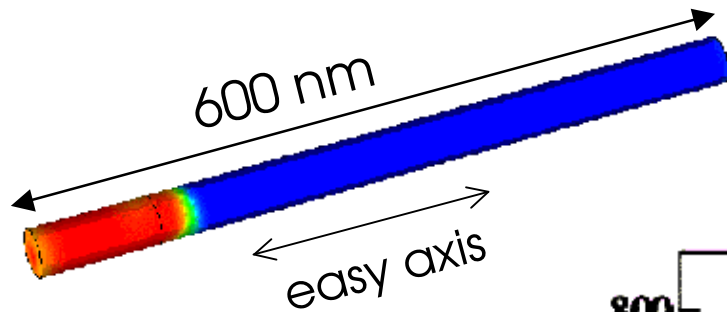
- Cells ($\text{Sm}_2\text{Co}_{17}$):
 $K_1 = 5 \text{ MJ/m}^3$
- Intercellular phase

Attractive pinning:
 $K_1 = 1.2 \text{ MJ/m}^3$

Repulsive pinning:
 $K_1 = 9.0 \text{ MJ/m}^3$

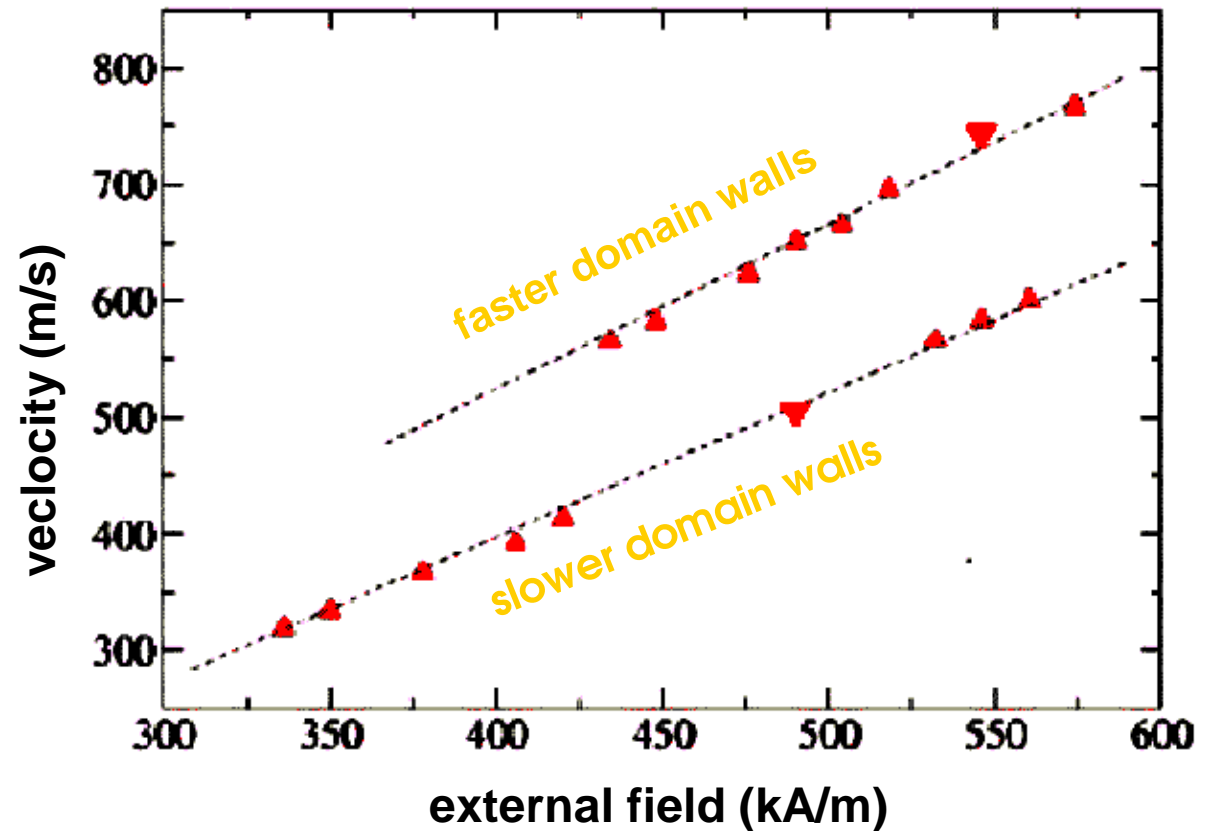
Domain Wall Motion

$D = 20 \text{ nm}, \alpha = 0.1$

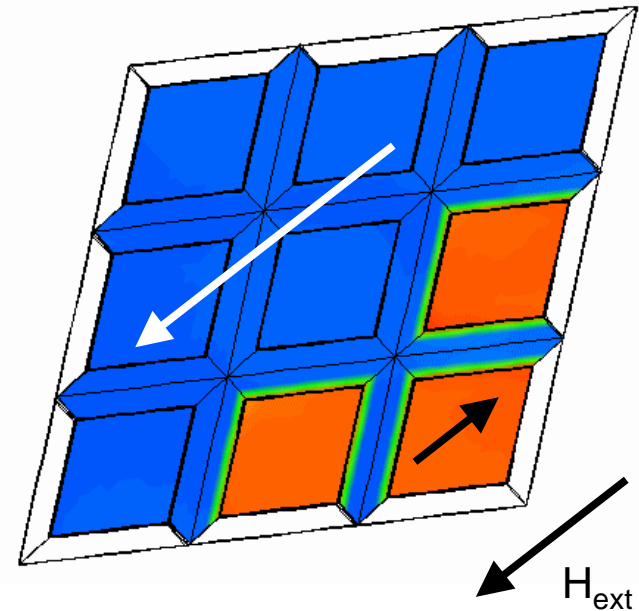
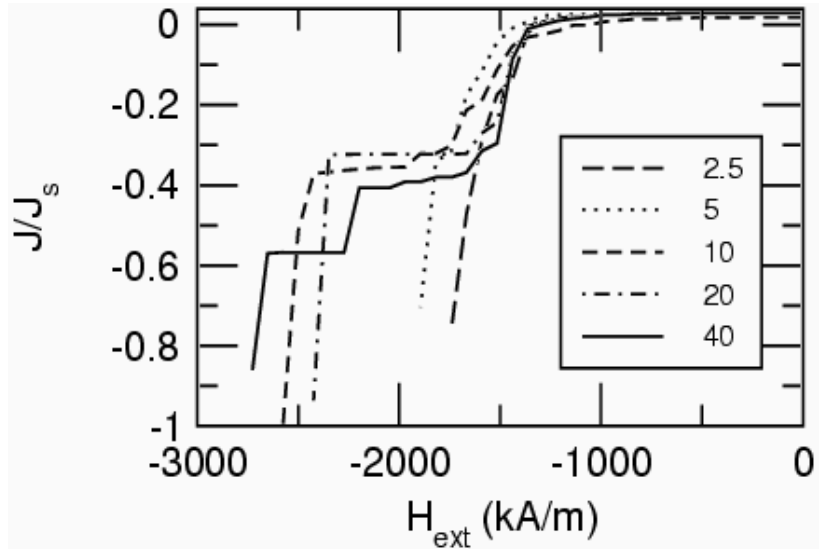


Co wire

$J_s = 1.76 \text{ T},$
 $K_1 = 0.45 \text{ MJ/m}^3$
 $A = 13 \text{ pJ/m}$



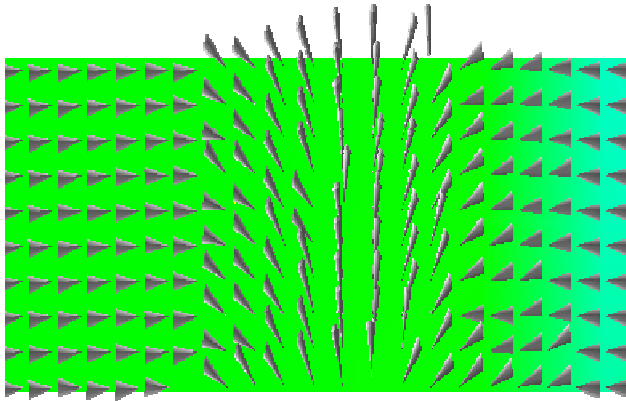
Thick Intercellular Phases



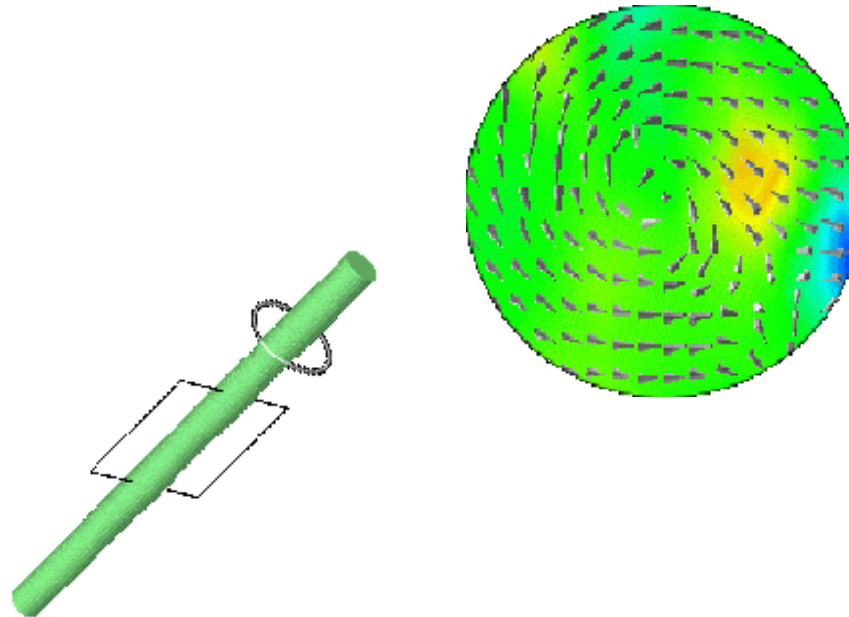
- Reversal of the whole intercellular phase
- Nucleation field of the cells determines H_c

Domain Wall Structure

transverse wall



vortex wall

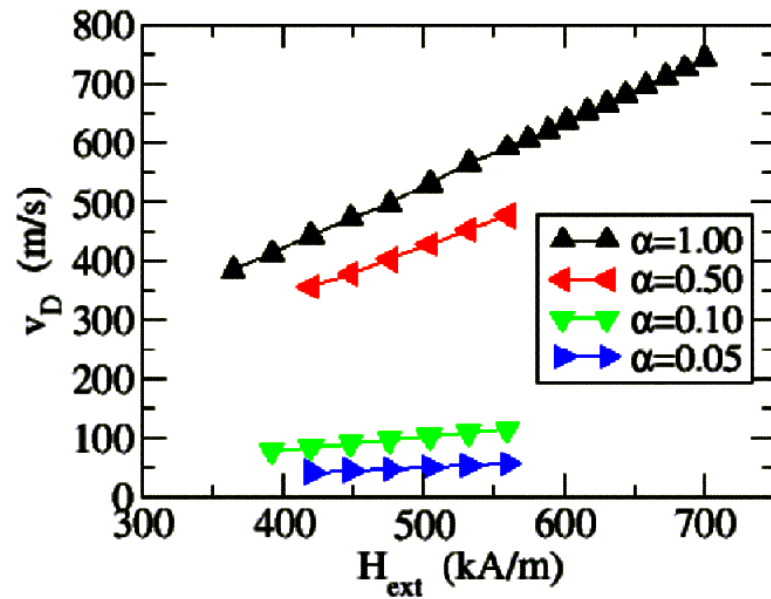


- $d \leq 20$ nm
- domain wall moves slower
- velocity decreases with decreasing damping

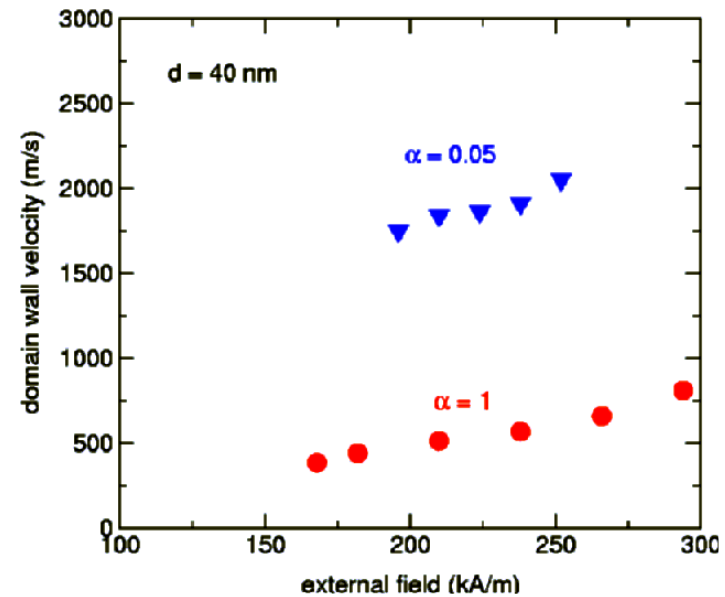
- $d \geq 20$ nm
- domain wall moves faster
- velocity increases with decreasing damping

Influence of Damping

transverse wall

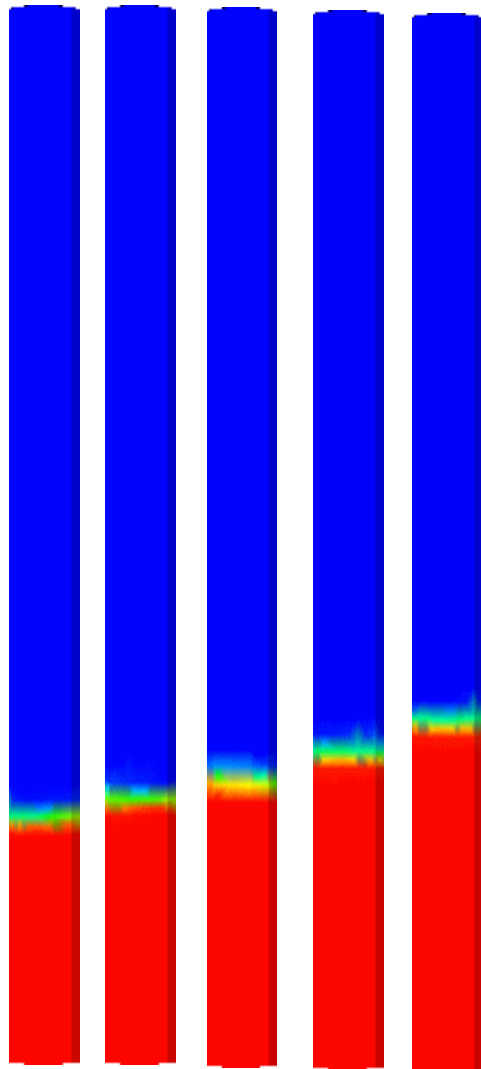


vortex wall

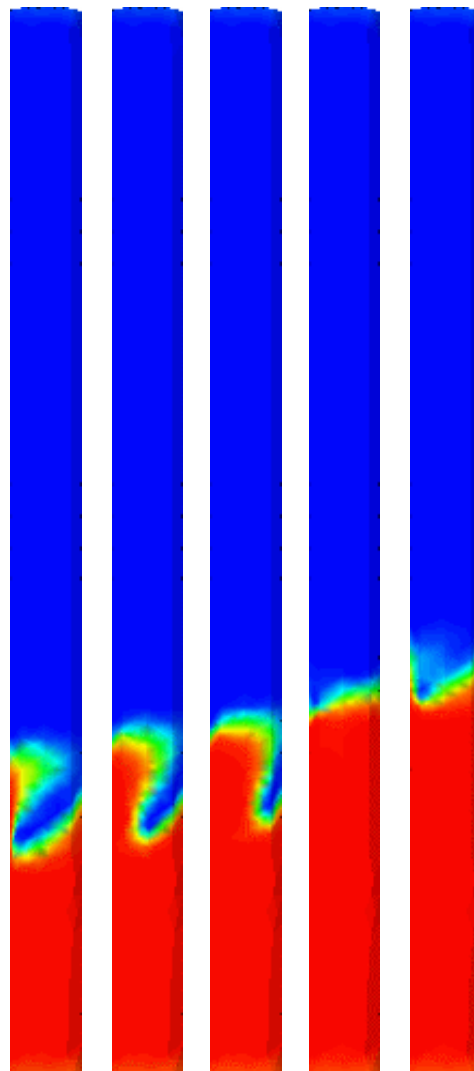


Domain Wall Motion

transverse wall



vortex wall



Simulation parameters:

- $d = 20 \text{ nm}$
- $\alpha = 1$
- $H_{\text{ext}} = 490 \text{ kA/m}$

Summary

Domain Wall Pinning

- Different pinning mechanisms depending on the composition
- Repulsive pinning: linear dependence of the pinning field on anisotropy

Domain Wall Motion

- Different wall configurations depending on the wire thickness
- high domain wall velocity
 - high damping in thin wires (transverse wall)
 - low damping in thick wires (vortex wall)

Acknowledgements

- **Austrian Science Fund FWF**
Y 132 – PHY: Advanced numerical micromagnetics
- **HITEMAG project**
GRD1-1999-11125: Novel Permanent Magnets for High Temperature Applications